

E-BLOW: E-Beam Lithography Overlapping aware Stencil Planning for MCC System Bei Yu, Kun Yuan<sup>†</sup>, Jhih-Rong Gao, and David Z. Pan

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# Electric Beam Lithography (EBL)

Promising candidate for next generation lithography process
 Variable Shaped Beam (VSB)

Charactor Projection (CP): a pattern is pre-designed on the stencil, then it can be printed in one electronic shot;

Key limitation: has been and still is the low throughput.



Multi-Column Cell (MCC) system

ILP formulation	
min T <sub>total</sub>	(2)
s.t $T_{total} \geq T_c^{VSB} - \sum_{i=1}^n (\sum_{k=1}^M R_{ic} \cdot a_{ik}), \ \forall c \in P$	(2 <i>a</i> )
$x_i + w_i \leq W,$ $\stackrel{i=1}{\forall i \in N}$	(2 <i>b</i> )
$\sum_{k}^{m}a_{ik}\leq 1, \qquad orall k\in M$	(2 <i>c</i> )
$x_i + w_{ij} - x_j \leq W(2 + p_{ij} - a_{ik} - a_{jk})$	(2 <i>d</i> )
$egin{aligned} & x_j + w_{ji} - x_i \leq W(3 - p_{ij} - a_{ik} - a_{jk}) \ & a_{ik}, a_{jk}, p_{ij}: 0 - 1  ext{ variable} \end{aligned}$	(2 <i>e</i> ) (2 <i>f</i> )

#### Symmetrical Blank (S-Blank) Assumption

E-BLOW for 1D-OSP (cont.)

the blanks of each character is symmetry (left slack = right slack).
 Note that for different characters *i* and *j*, their slacks s<sub>i</sub> and s<sub>j</sub> can be different.

#### Theorem

Under S-Blank assumption, the greedy approach can get maximum overlapping space  $\sum_{i} s_{i} - \max\{s_{i}\}$ .

# **E-BLOW for 2D-OSP**

**Overall Flow** 



Simulated annealing based framework.
Sequence Pair as topology representation.
Pre-filter process to remove bad characters.
Clustering is applied to achieve speedup.

**KD-Tree based Clustering** 

(3)

(3*a*)

(3*b*)

(3*c*)

(3')

(3*a*′)

(4)



Several independent character projections (CP) are used to further speed-up the writing process.

- Each CP is applied on one section of wafer, and all CPs can work parallelly to achieve better throughput.
- Different CPs share one stencil design.

# **Problem Formulation**

## **Some Definitions**

In an MCC system with *P* CPs, the whole wafer is divided into *P* regions  $\{w_1, w_2, \ldots, w_P\}$ , and each region is written by one particular CP. For each character candidate  $c_i \in C^C$ , its writing time through VSB mode is denoted as  $n_i$ , while its writing time through CP mode is 1. Suppose  $c_i$  repeats  $t_{ic}$  times on region  $w_c$ . Let  $a_i$  indicate whether  $c_i$  is selected. Therefore, for region  $w_c$  the total writing time  $T_c$  is as follows:



problem:

$$\max \sum_{i} \sum_{j} (w_{i} - s_{i}) \cdot a_{ij} \cdot ratio_{i}$$
  
s.t. 
$$\sum_{i} (w_{i} - s_{i}) \cdot a_{ij} \leq W - max_{s}$$
$$(3c) - (3d)$$

where  $ratio_i = profit_i/(w_i - s_i)$ , and  $max_s$  is the maximum horizontal slack length of every character, i.e.  $max_s = max\{s_i | i = 1, 2, ..., n\}$ .

### Lemma

If each *ratio<sub>i</sub>* is the same, the multiple knapsack problem (3') can find a 1/2-approximation algorithm using LP Rounding method.

#### Theorem

The LP Rounding solution of (3) can be a  $0.5/\alpha$  – approximation to



(3*d*) Speed-up the process of finding available pair  $(c_i, c_j)$ ; From O(n) to O(logn); For  $c_2$ , to find another candidate with the similar space, only scan  $c_1 - c_5$ .

# **Experimental Results**

Implemented in C++
 Intel Core 3.0GHz Linux machine with 32G RAM
 GUROBI as linear programming (LP) solver

### Shot Number Comparison



 $T_{c} = \sum_{i=1}^{n} a_{i} \cdot (t_{ic} \cdot 1) + \sum_{i=1}^{n} (1 - a_{i}) \cdot (t_{ic} \cdot n_{i})$  $= \sum_{i=1}^{n} t_{ic} \cdot n_{i} - \sum_{i=1}^{n} t_{ic} \cdot (n_{i} - 1) \cdot a_{i} = T_{c}^{VSB} - \sum_{i=1}^{n} R_{ic} \cdot a_{i}$ 

The total writing time of the MCC system is formulated as follows:

$$T_{total} = \max\{T_c\} = \max\{T_c^{VSB} - \sum_{i=1}^n R_{ic} \cdot a_i\}, \forall c \in P$$

**Overlapping aware Stencil Planning (OSP) for MCC system** Given a set of character candidate  $C^C$ , select a subset  $C^{CP}$  out of  $C^C$  as characters, and place them on the stencil. The objective is to minimize the total writing time  $T_{total}$  expressed by (1), while the placement of  $C^{CP}$  is bounded by the outline of stencil. The width and height of stencil is W and H, respectively.

# 1D-OSP and 2D-OSP





# program (3').

**Successive Relaxation** Because of the reasonable LP rounding property, we propose a successive relaxation algorithm to solve program (3) iteratively.

# Algorithm: SuccRounding( thinv )

## **Require:** ILP Formulation (3)

1: set all a<sub>ij</sub> to variables;

2: repeat

- 3: update *profit<sub>i</sub>* for all variables  $a_{ij}$ ;
- 4: solve relaxed LP of (3);

5: repeat

- 6: find  $a_{pq} = \max\{a_{ij}, \text{ and } c_i \text{ can insert into row } r_j\};$
- 7: for all  $a_{ij} \ge a_{pq} \times th_{inv}$  do
- 8: **if**  $c_i$  can be assigned to row  $r_j$  **then**
- 9:  $a_{ij} = 1$  and set it to a non-variable;
- 10: Update capacity of row  $r_j$ ;
- 11: **end if**
- 12: **end for**
- 13: **until** cannot find  $a_{pq}$
- 14: **until**

One key step of the Algorithm is the *profit<sub>i</sub>* update (line 3). For each character  $c_i$ , we set its *profit<sub>i</sub>* as follows:

$$\textit{orofit}_i = \sum_{c} \frac{t_c}{t_{max}} \cdot (n_i - 1) \cdot t_{ic}$$

where  $t_c$  is current writing time of region  $w_c$ , and  $t_{max} = \max \{t_c, \forall c \in P\}$ . Through

For 1D cases, the greedy algorithm introduces 47% more shots number, and [TCAD'12] introduces 19% more shots number.



For 2D cases, greedy introduces 30% more shot number, while [TCAD'12] introduces 14% more shot number.

### **CPU Runtime Comparison**

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# (a) (b) **Figure : (a) 1D-OSP; (b) 2D-OSP.**

### **E-BLOW for 1D-OSP**



Novel iterative solving framework to search near-optimal solution
 Linear programming (LP) relaxation with lower bound theoretically
 Successive rounding

Dynamic programming based refinement

applying the *profit<sub>i</sub>*, the region  $w_c$  with longer writing time would be considered more during the LP formulation.

**1D-OSP Refinement** Simplified formulation and successive relaxation are under the symmetrical blank assumption. Although it can be effectively solved, for asymmetrical cases it would lose some optimality. To compensate the losing, we present a dynamic programming based refinement procedure.

## Algorithm: Refine(k)

- 1: if k = 1 then
- 2: Generate partial solution  $(w_1, sl_1, sr_1)$ ;
- 3: **else**
- 4: **Refine(k-1);**
- 5: for each partial solution (w, I, r) do
- 6:  $(W_1, I_1, r_1) = (W + W_k \min(sr_k, I), sI_k, r);$
- 7:  $(W_2, I_2, r_2) = (W + W_k \min(sI_k, r), I, sr_k);$
- 8: Replace (w, I, r) by  $(w_1, I_1, r_1)$  and  $(w_2, I_2, r_2)$ ;
- 9: **if** solution set size  $\geq$  threshold **then**
- 10: SolutionPruning();
- 11: **end if**
- 12: **end for**
- 13: **end if**



Compared with [TCAD'12], E-BLOW can reduce 34.3% of runtime for 1D cases, while  $2.8 \times$  speedup for 2D cases.

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